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Attorney Docket No. 5649-874

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Hag-ju Cho
Serial No.: 09/893,035
Filed: June 27, 2001

Group Art Unit: 2813
Examiner: Erik J. Kielin

For: METHODS OF MANUFACTURING INTEGRATED CIRCUIT DEVICES
THAT INCLUDE A METAL OXIDE LAYER DISPOSED ON ANOTHER
LAYER TO PROTECT THE OTHER LAYER FROM DIFFUSION OF
IMPURITIES AND INTEGRATED CIRCUIT DEVICES
MANUFACTURED USING SAME

Date: July 1, 2002

Box NON-FEE AMENDMENT
Commissioner for Patents
Washington, DC 20231

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AMENDMENT

Sir:

This is a full and timely response to the non-final Office Action mailed April 1, 2002 that contains amendments and remarks as set forth hereafter. Attached hereto is a marked up version of the changes made to the Claims by the current amendments. The marked up version of the changes is captioned "**VERSION WITH MARKINGS TO SHOW CHANGES MADE.**"

In the Claims:

Please enter amended Claims 1, 2, and 10 as follows:

B1
SUB
C1

1. (Amended) A method of manufacturing an integrated circuit device, comprising:
forming an insulation layer that comprises oxygen between upper and lower conductive layers, the insulation layer having a first surface portion that is exposed by the upper and lower conductive layers and a second, non-exposed, surface portion;
and
exposing the insulation layer to a metal precursor that is reactive with oxygen so as to form a first metal oxide layer on the first surface portion of the insulation layer without forming the first metal oxide layer on the second surface portion of the insulation layer.

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